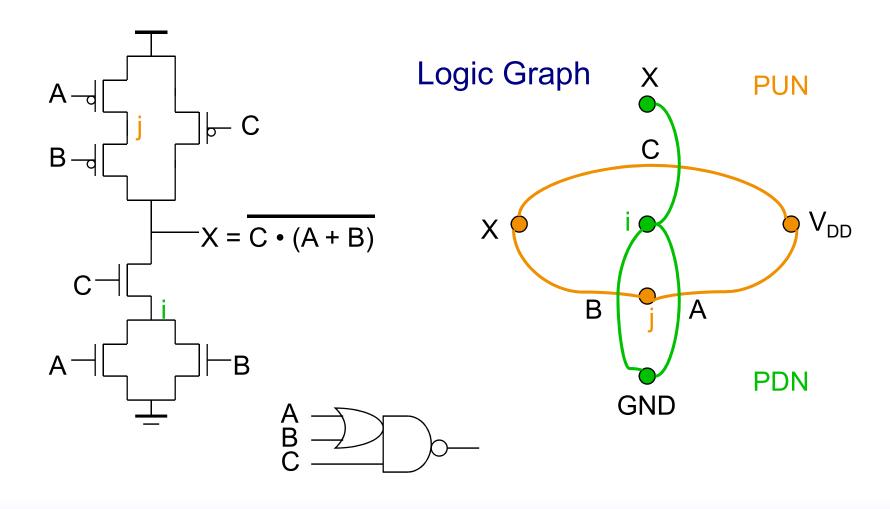
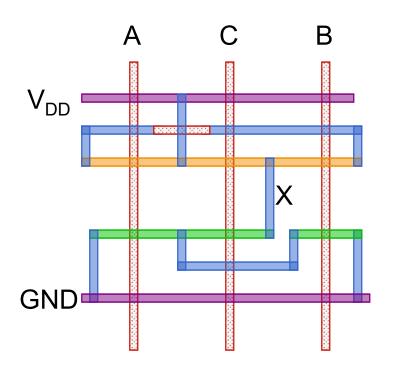
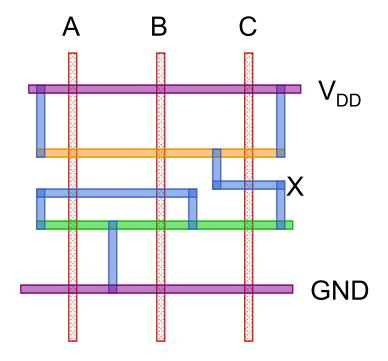
Stick Diagrams

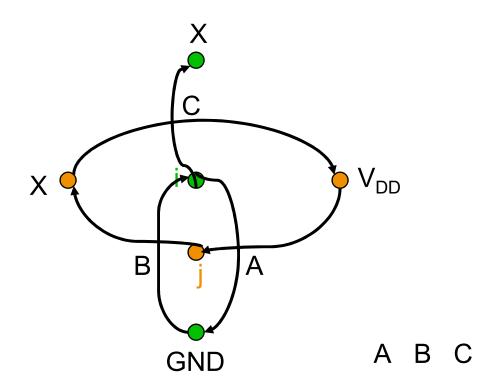


Two Versions of C • (A + B)

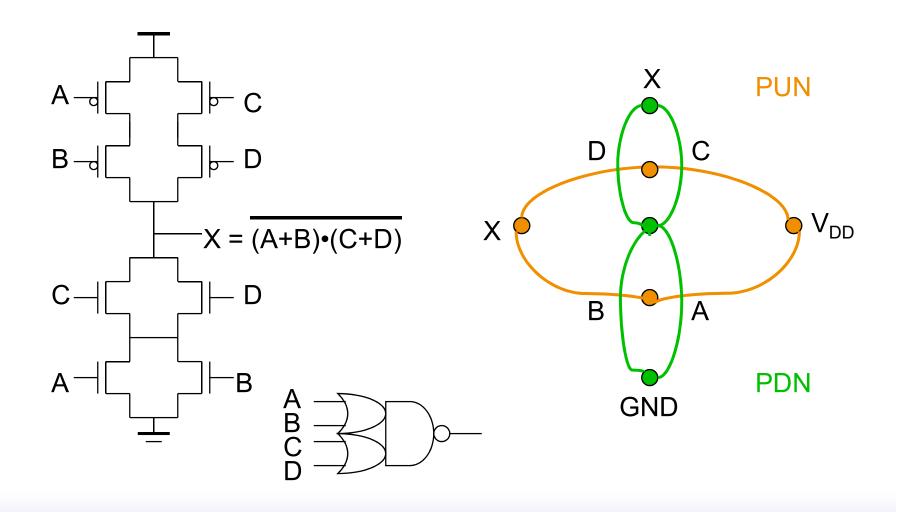




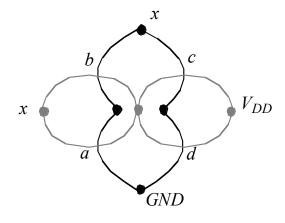
Consistent Euler Path



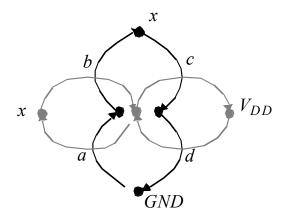
OAI22 Logic Graph



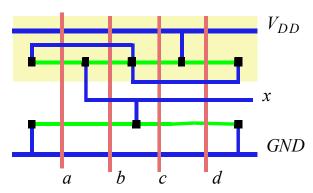
Example: x = ab+cd



(a) Logic graphs for $\overline{(ab+cd)}$



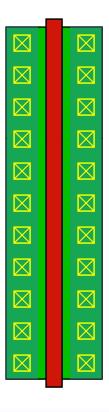
(b) Euler Paths $\{a \ b \ c \ d\}$



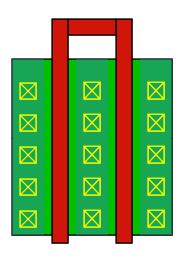
(c) stick diagram for ordering {a b c d}

Multi-Fingered Transistors

One finger



Two fingers (folded)



Less diffusion capacitance

Properties of Complementary CMOS Gates Snapshot

High noise margins:

 V_{OH} and V_{OL} are at V_{DD} and GND, respectively.

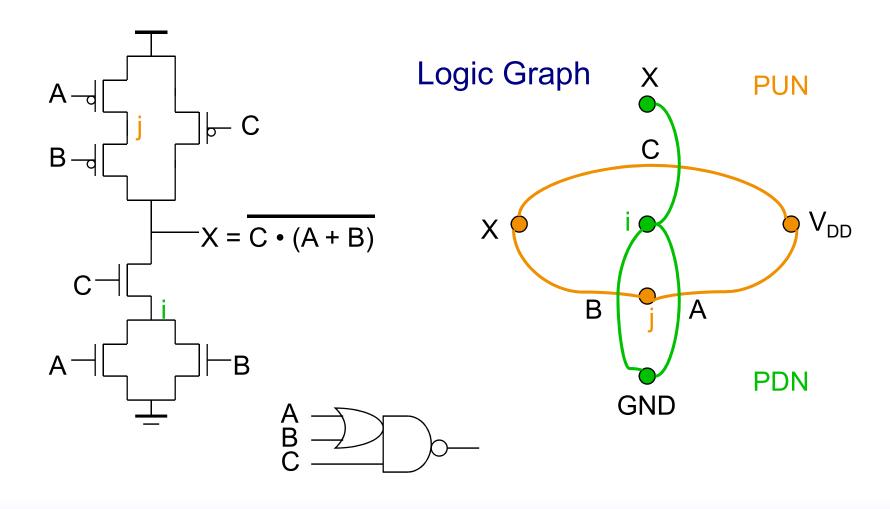
No static power consumption:

There never exists a direct path between V_{DD} and V_{SS} (GND) in steady-state mode.

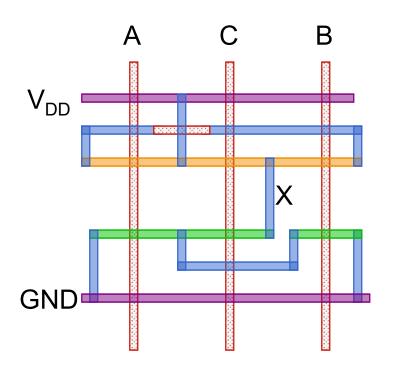
Comparable rise and fall times:

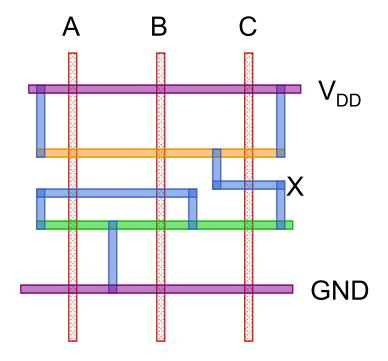
(under appropriate sizing conditions)

Stick Diagrams

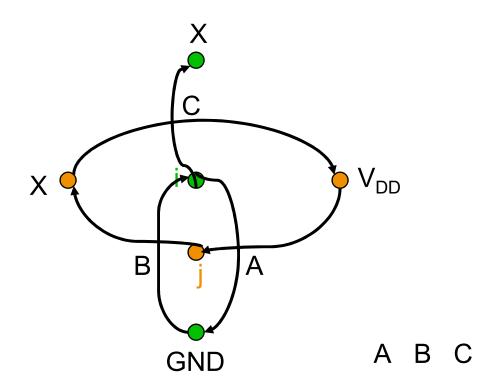


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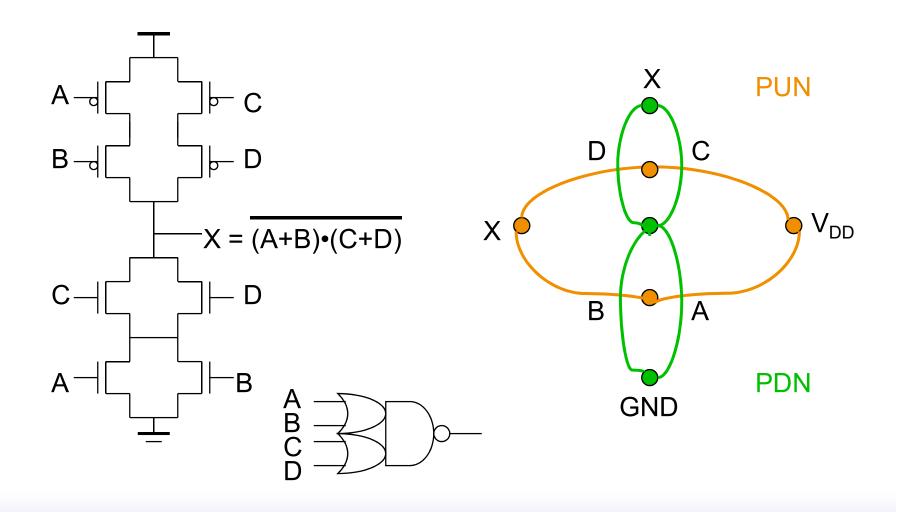




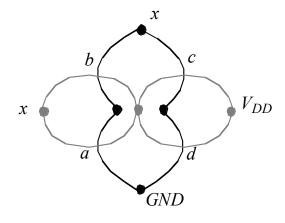
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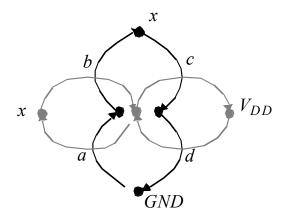
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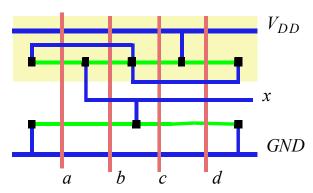
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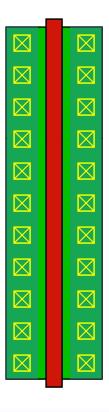
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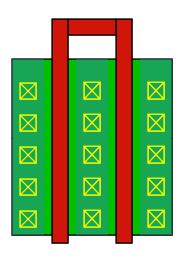
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